

LISTING OF THE CURRENT CLAIMS
IN ACCORDANCE WITH REVISED AMENDMENT PRACTICE

Claims 1-66: Canceled.

67. (Currently Amended) A three-dimensional physical vapor deposition target, comprising:
a material comprising ~~one or more of Cu, Ni, Co, Ta, Al, and Ti~~ copper;
an average grain size of less than or equal to 250 microns within the material;
a shape, the shape including at least one cup having a first end and a second end in opposing relation to the first end; the first end having an opening extending therein; the cup having a hollow therein; the hollow extending from the opening in the first end toward the second end; the cup having an interior surface defining a periphery of the hollow and an exterior surface extending around the second end at rounded corners; and
a sputtering surface defined along the interior surface of the cup, wherein the target is three-dimensional~~[],]]~~ and monolithic and comprises a cast ingot.

68. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of copper; and wherein the target consists essentially of the material.

69. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of tantalum; and wherein the target consists essentially of the material.

70. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of CuSn, with the Sn being present to from about 100 ppm, by weight, to about 3 atomic percent; and wherein the target consists essentially of the material.

71. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of CuAl, with the Al being present to from about 100 ppm, by weight, to about 3 atomic percent; and wherein the target consists essentially of the material.
72. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of CuAg, with the Ag being present to from about 100 ppm, by weight, to about 3 atomic percent; and wherein the target consists essentially of the material.
73. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the average grain size is less than or equal to 200 microns.
74. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the average grain size is less than or equal to 100 microns.
75. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the average grain size is less than or equal to 90 microns.
76. (Original) The three-dimensional vapor deposition target of claim 67 wherein the average grain size is less than or equal to 85 microns.

Claims 77-89: Canceled.